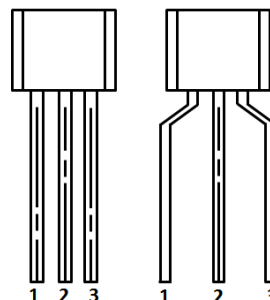


**SENSITIVE GATE TRIACS
SILLICON BIDIRECTIONAL THYRISTORS**
**TRIACS
1.0 AMPERES RMS
400 thru 600 VOLTS**
FEATURES

- One-piece, injection-molded package
- Blocking voltage to 600volts.
- Sensitive gate Triggering in four trigger modes (quadrants) for all possible combinations of trigger sources, and especially for circuits that source gate drives.
- All diffused and glassivated junctions for maximum uniformity of parameters and reliability.
- Improved noise immunity (dv/dt minimum of 20 V/msec at 110°C)
- High surge current of 10 amps
- Pb-Free package

TO-92 (TO-226AA)

PIN ASSIGNMENT

1	Main terminal 1
2	Gate
3	Main terminal 2

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

PARAMETER	SYMBOL	VALUE	UNIT
Peak repetitive off-state voltage $T_J = -40^{\circ}\text{C}$ to 110°C , sine wave, 50 to 60 Hz, gate open (Note 1)	V_{DRM} V_{RRM}	400 600	V
On-state RMS current full cycle sine wave 50 to 60 Hz @ $T_C = 50^{\circ}\text{C}$	$I_{T(RMS)}$	1.0	A
Peak non-repetitive surge current full cycle sine wave 60Hz @ $T_J = 25^{\circ}\text{C}$	I_{TSM}	10.0	A
Circuit fusing consideration @ $T = 8.3$ ms	I^2t	0.40	A ² S
Peak gate power, $t \leq 2.0\mu\text{s}$ @ $T_C = 80^{\circ}\text{C}$	P_{GM}	5.0	W
Average gate power, $t \leq 8.3\text{ms}$ @ $T_C = 80^{\circ}\text{C}$	P_{GAV}	0.1	W
Peak gate current, $t \leq 2.0\mu\text{s}$ @ $T_C = 80^{\circ}\text{C}$	I_{GM}	1.0	A
Peak gate voltage, $t \leq 2.0\mu\text{s}$ @ $T_C = 80^{\circ}\text{C}$	V_{GM}	5.0	V
Operating junction temperature range	T_J	-40 to +110	$^{\circ}\text{C}$
Storage temperature range	T_{STG}	-40 to +150	$^{\circ}\text{C}$

Notes:

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

REV.6 Mar.-2019, KTXD11

RATING AND CHARACTERISTIC CURVES

T1M5F-A SERIES

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE	UNIT
Thermal resistance junction to lead	R_{thJL}	60	$^{\circ}\text{C}/\text{W}$
Thermal resistance junction to case	R_{thJC}	75	$^{\circ}\text{C}/\text{W}$
Thermal resistance junction to ambient	R_{thJA}	150	$^{\circ}\text{C}/\text{W}$
Maximum lead temperature for soldering purposes 1/8 for case for 10 seconds	T_L	260	$^{\circ}\text{C}$

OFF CHARACTERISTICS

PARAMETER	SYMBOL	MIN	TYP.	MAX	UNIT
Peak repetitive forward or reverse blocking current $V_D = \text{rated } V_{DRM} \text{ and } V_{RRM}, \text{ gate open}$	I_{DRM} I_{RRM}	---	---	10 100	μA

ON CHARACTERISTICS

PARAMETER	SYMBOL	MIN	TYP.	MAX	UNIT
Peak forward on-state voltage ($I_{TM} = \pm 1\text{A peak @ } T_P \leq 2.0\text{ ms, duty cycle } \leq 2\%$)	V_{TM}	---	---	1.9	V
Gate trigger current ($V_D = 12\text{ V}_{dc}, R_L = 100\text{ ohms}$)	I_{GT1} I_{GT2} I_{GT3} I_{GT4}	---	---	5.0 5.0 5.0 7.0	mA
Holding current ($V_D = 12\text{ V}$, initiating current = $\pm 200\text{ mA}$)	I_H	---	1.5	10	mA
Turn-on time ($V_D = \text{rated } V_{DRM}, I_{TM} = 1.0\text{A pk}, I_G = 25\text{ mA}$)	t_{gt}	---	2	---	μs
Gate trigger voltage ($V_D = 12\text{ V}_{dc}, R_L = 100\text{ ohms}$)	V_{GT1} V_{GT2} V_{GT3} V_{GT4}	---	0.66 0.77 0.84 0.88	2.0 2.0 2.0 2.5	V
Latching current ($V_D = 12\text{ V}, I_G = 10\text{ mA}$)	I_{L1} I_{L2} I_{L3} I_{L4}	---	1.6 10.5 1.5 2.5	15 20 15 15	mA
Gate non-trigger voltage ($V_D = 12\text{ V}, R_L = 100\text{ ohms}, T_J = 110^{\circ}\text{C}$)	V_{GD}	1.0	---	---	V

DYNAMIC CHARACTERISTICS

PARAMETER	SYMBOL	MIN	TYP.	MAX	UNIT
Critical rate of rise of off-state voltage ($V_D = \text{rated } V_{DRM}$, exponential waveform, gate open, $T_J = 110^{\circ}\text{C}$)	dv/dt	20	60	---	V/ μs

RATING AND CHARACTERISTIC CURVES T1M5F-A SERIES

FIG.1- RMS current derating versus ambient temperature

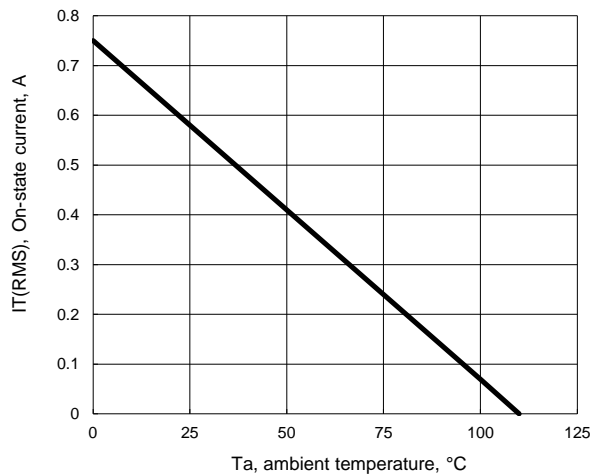


FIG.2- RMS current derating versus case temperature

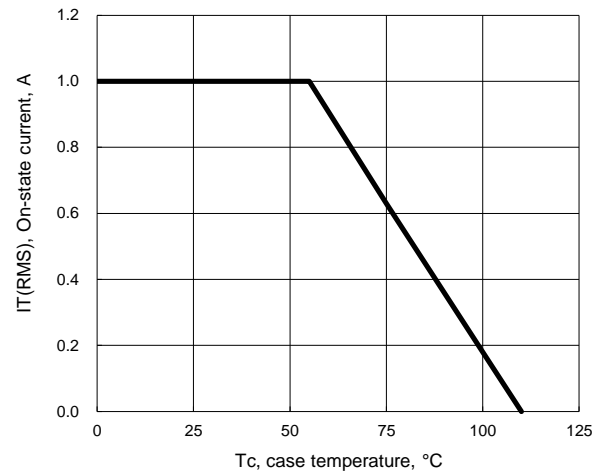


FIG.3- Power dissipation

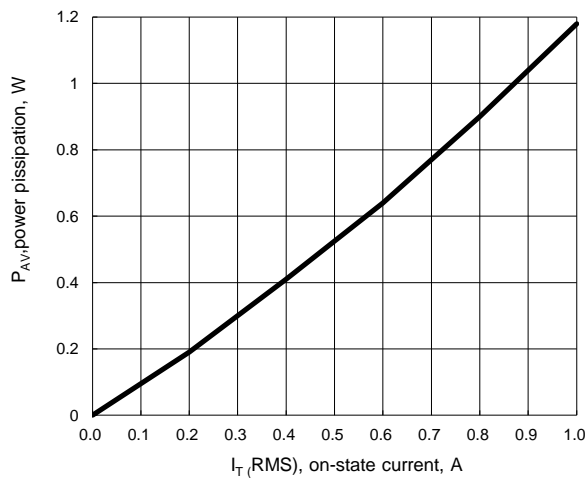


FIG.4- On-state characteristics

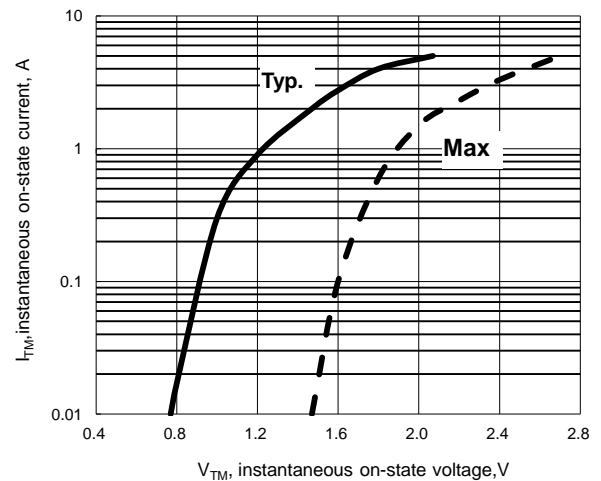


FIG.5- Transient thermal response

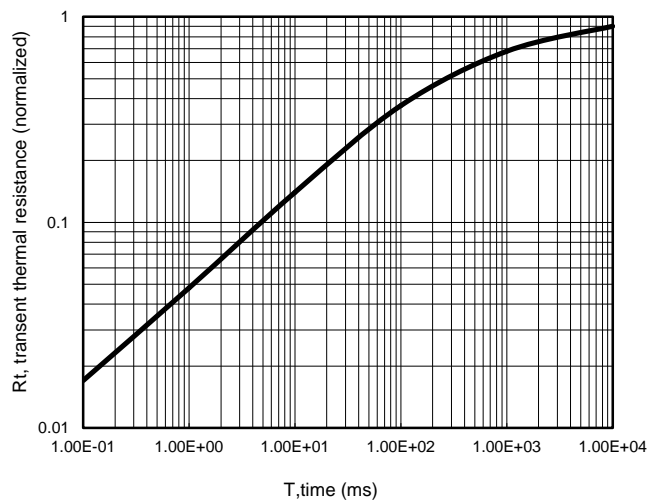
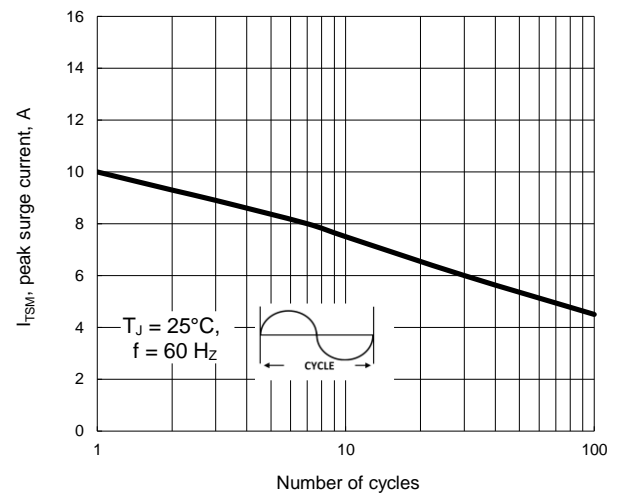


FIG.6- Maximum allowable surge current



RATING AND CHARACTERISTIC CURVES
T1M5F-A SERIES

FIG.7- Typical gate trigger current versus
junction temperature

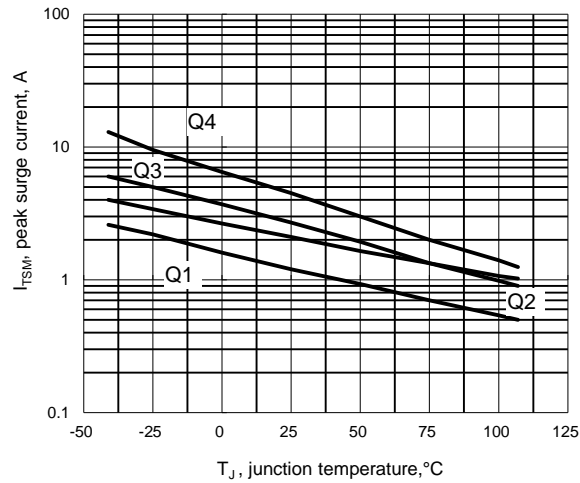


FIG.8- Typical gate trigger current versus
junction temperature

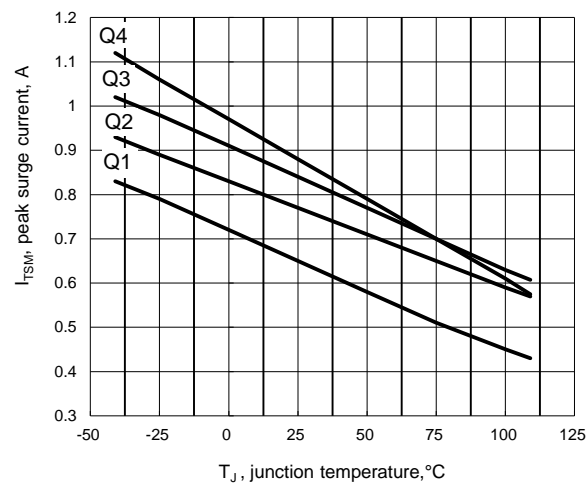


FIG.9- Typical latching current versus
junction temperature

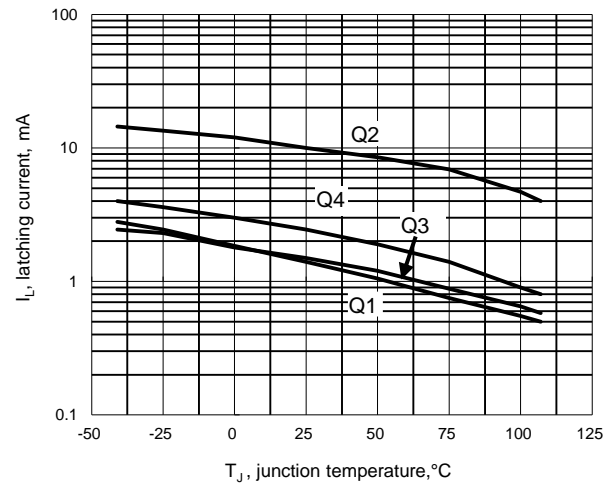
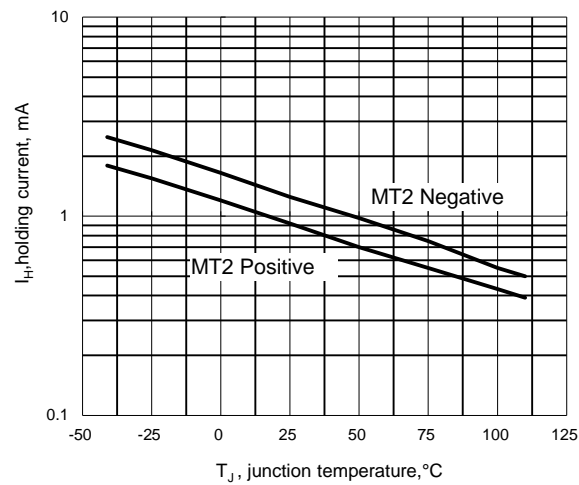
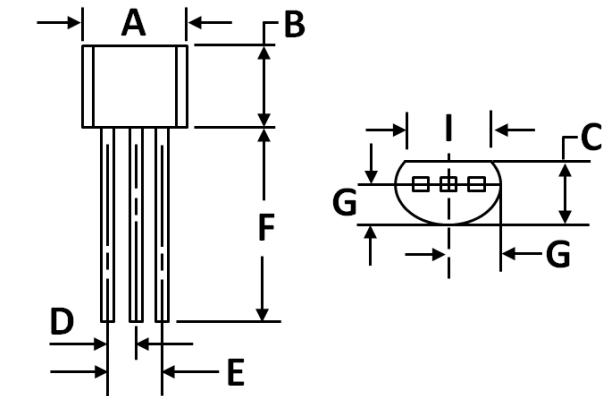


FIG.10- Typical holding current versus
junction temperature

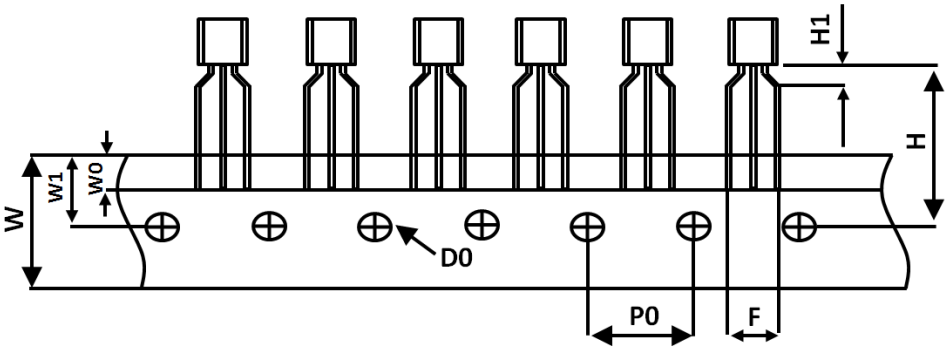


Bulk Packaging :



DIM.	MIN.	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	1.15	1.39
E	2.42	2.66
F	12.7	--
G	2.04	2.66
I	3.43	--
All dimensions in millimeter		

Reel Packaging :



DIM.	INCHES		MILLIMETERS	
	MIN.	MAX	MIN.	MAX
P0	0.488	0.512	12.4	13.0
H	0.728	0.768	18.5	19.5
H1	0.079	0.118	2.0	3.0
F	0.188	0.212	4.78	5.38
D0	Ø0.150	Ø0.165	Ø3.8	Ø4.2
W	0.701	0.717	17.8	18.2
W0	0.228	0.244	5.8	6.2
W1	0.346	0.362	8.8	9.2

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